Dual Channel OptoHiT™ Series, High-Temperature Phototransistor Optocoupler in Small Outline 8-Pin Package

FOD8802 Series

Description

The FOD8802 dual channel optocoupler is a best-in-class phototransistor, optocoupler utilizing ON Semiconductor leading-edge proprietary process technology to achieve high operating temperature performance, up to 125°C. It consists of two aluminum gallium arsenide (AlGaAs) infrared light emitting diode optically coupled to two phototransistors, in a small outline, 8-pin SOIC package. It delivers consistent current transfer ratio at very low input current over temperature. The AlGaAs light ouput degradation performance is significantly better than the commodity optocoupler products that uses the standard GaAs, extending lifetime and reducing the guardband requirements to compensate for temperature drift. The input–output isolation voltage, Viso, is rated at 2500 VAC_{RMS}.

Features

- Excellent CTR Linearity at High Temperature
- CTR at Very Low Input Current, I_F
- High Isolation Voltage Regulated by Safety Agency, UL1577, 2500 VAC_{RMS} for 1 min.
- Applicable to Infrared Ray Reflow, 260°C
- These are Pb-Free Devices

Typical Applications

- Primarily Suited for DC-DC Converters
- For Ground Loop Isolation, Signal to Noise Isolation
- Communications Adapters, Chargers
- Consumer Appliances, Set Top Boxes
- Industrial Power Supplies, Motor Control, Programmable Logic Control



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M SUFFIX CASE 751DZ



1. ON = Corporate Name

2. 8802x = Device Number

3. V = DIN EN/IEC60747-5-5 Option

4. X = One–Digit Year Code

YY = Digit Work Week
S = Assembly Package Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 9 of this data sheet.

Table 1. SAFETY AND INSULATION RATINGS

As per DIN_EN/IEC60747-5-5. this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE 0110/1.89 Table 1,	< 150 V _{RMS}	I–IV
For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification	40/125/21	
Pollution Degree (DIN VDE 0110/1.89)	2	
Comparative Tracking Index	175	

Symbol	Parameter	Value	Unit
VPR	Input-to-Output Test Voltage, Method A, V_{IORM} x 1.6 = V_{PR} , Type and Sample Test with t_m = 10 s, Partial Discharge < 5 pC	904	Vpeak
	Input–to–Output Test Voltage, Method B, $V_{\rm IORM}$ x 1.875 = $V_{\rm PR}$, 100% Production Test with t_m = 1 s, Partial Discharge < 5 pC	1060	Vpeak
VIORM	Maximum Working Insulation Voltage	565	Vpeak
VIOTM	Highest Allowable Over-Voltage	4,000	Vpeak
	External Creepage	≥ 4	mm
	External Clearance	≥ 4	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
Τ _S	Case Temperature (Note 1)	150	°C
IS,INPUT	Input Current (Note 1)	200	mA
PS,OUTPUT	Output Power (Note 1)	300	mW
Rio	Insulation Resistance at T_S , V_{IO} = 500 V (Note 1)	> 10 ⁹	Ω

1. Safety limit values - maximum values allowed in the event of a failure.

Table 2. ABSOLUTE MAXIMUM RATINGS (T_A = $25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Value	Units
T _{STG}	Storage Temperature	-40 to +150	°C
T _{OPR}	Operating Temperature	-40 to +125	°C
TJ	Junction Temperature	–50 to +150	°C
T _{SOL}	Lead Solder Temperature (Refer to Reflow Temperature Profile)	260 for 10 sec	°C

EMITTER

I _{F(average)}	Continuous Forward Current	20	mA
V _R	Reverse Input Voltage	6	V
PD _{LED}	Power Dissipation (Note 2)	40	mW

DETECTOR

I _{C(average)}	Continuous Collector Current	30	mA
V _{CEO}	Collector-Emitter Voltage	75	V
V _{ECO}	Emitter-Collector Voltage	7	V
PD _C	Collector Power Dissipation (Note 2)	150	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.

Table 3. ELECTRICAL CHARACTERISTICS

Apply over all recommended conditions ($T_A = -40^{\circ}C$ to $+125^{\circ}C$ unless otherwise specified). All typical values are measured at $T_A = 25^{\circ}C$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _F	Forward Voltage	I _F = 1 mA	1.0	1.35	1.8	V
$\Delta V_{F}^{/} \Delta T_{A}$	Forward Voltage Coefficient	I _F = 1 mA		-1.6		mV/°C
I _R	Reverse Current	V _R = 6 V			10	μΑ
CT	Terminal Capacitance	V = 0 V, f = 1 MHz		30		pF
BV _{CEO}	Collector-Emitter Breakdown Voltage	l _C = 0.5 mA, l _F = 0 mA	75	130		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 100 μA, I _F = 0 mA	7	12		V
I _{CEO}	Collector Dark Current	V_{CE} = 75 V, I _F = 0 mA, T _A = 25°C			100	nA
		$V_{CE} = 50 \text{ V}, \text{ I}_{\text{F}} = 0 \text{ mA}$			50	μΑ
		$V_{CE} = 5 V$, $I_F = 0 mA$			30	μΑ
C _{CE}	Capacitance	$V_{CE} = 0 V$, f = 1 MHz		8		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Table 4. TRANSFER CHARACTERISTICS

Apply over all recommended conditions ($T_A = -40^{\circ}C$ to $+125^{\circ}C$ unless otherwise specified). $T_A = 25^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Device	Conditions	Min.	Тур.	Max.	Units	
				I_F = 1.0 mA, V_{CE} = 5 V @ T_A = 25°C	80	120	160	
		FODeeooA	I _F = 1.0 mA, V _{CE} = 5 V	35	120	230		
		FOD8802A	I _F = 1.6 mA, V _{CE} = 5 V	40	125			
			I _F = 3.0 mA, V _{CE} = 5 V	45	138			
			$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V} @ T_A = 25^{\circ}\text{C}$	130	195	260		
		FODeeooB	I _F = 1.0 mA, V _{CE} = 5 V	65	195	360		
		FOD8802B	I _F = 1.6 mA, V _{CE} = 5 V	70	202			
	Current Transfer Ratio		I _F = 3.0 mA, V _{CE} = 5 V	75	215		0/	
CTR _{CE}	(collector-emiiter)		$I_F = 1.0 \text{ mA}, V_{CE} = 5 \text{ V} @ T_A = 25^{\circ}\text{C}$	200	300	400	%	
		FOD8802C	I _F = 1.0 mA, V _{CE} = 5 V	100	300	560		
		FUD8802C	I _F = 1.6 mA, V _{CE} = 5 V	110	312			
			I _F = 3.0 mA, V _{CE} = 5 V	115	330			
			I_F = 1.0 mA, V_{CE} = 5 V @ T_A = 25°C	100		400		
		FOD0000D	I _F = 1.0 mA, V _{CE} = 5 V	45		560		
		FOD8802D	I _F = 1.6 mA, V _{CE} = 5 V	50				
			I _F = 3.0 mA, V _{CE} = 5 V	55				
	Saturated Current		$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V} @ T_A = 25^{\circ}\text{C}$	65	108	150	- %	
		FOD8802A	I _F = 1.0 mA, V _{CE} = 0.4 V	30	108			
			I _F = 1.6 mA, V _{CE} = 0.4 V	25	104			
			I _F = 3.0 mA, V _{CE} = 0.4 V	20	92			
		FOD8802B	$I_F = 1.0 \text{ mA}, V_{CE} = 0.4 \text{ V} @ T_A = 25^{\circ}\text{C}$	90	168	245		
			I _F = 1.0 mA, V _{CE} = 0.4 V	45	168			
			I _F = 1.6 mA, V _{CE} = 0.4 V	40	155			
			I _F = 3.0 mA, V _{CE} = 0.4 V	35	132			
CTR _{CE(SAT)}	Transfer Ratio (collector-emiiter)		I _F = 1.0 mA, V _{CE} = 0.4 V @ T _A = 25°C	140	238	380		
			I _F = 1.0 mA, V _{CE} = 0.4 V	75	238			
		FOD8802C	I _F = 1.6 mA, V _{CE} = 0.4 V	65	215			
			I _F = 3.0 mA, V _{CE} = 0.4 V	55	177			
			I _F = 1.0 mA, V _{CE} = 0.4 V @ T _A = 25°C	70		380		
			I _F = 1.0 mA, V _{CE} = 0.4 V	35				
		FOD8802D	I _F = 1.6 mA, V _{CE} = 0.4 V	30			1	
			I _F = 3.0 mA, V _{CE} = 0.4 V	25			-	
			I _F = 1.0 mA, I _C = 0.3 mA		0.17	0.40		
		FOD8802A	I _F = 1.6 mA, I _C = 0.4 mA		0.16	0.40		
		TODOODZA	I _F = 3.0 mA, I _C = 0.6 mA		0.15	0.40	-	
			I _F = 1.0 mA, I _C = 0.45 mA		0.17	0.40	_	
		FOD8802B	$I_{\rm F} = 1.6 \rm{mA}, I_{\rm C} = 0.6 \rm{mA}$		0.16	0.40		
			$I_{\rm F} = 3.0 \text{ mA}, I_{\rm C} = 1.0 \text{ mA}$		0.16	0.40		
V _{CE(SAT)}	Saturation voltage		I _F = 1.0 mA, I _C = 0.75 mA		0.18	0.40	V	
		FOD8802C	$I_F = 1.6 \text{ mA}, I_C = 1.0 \text{ mA}$		0.17	0.40		
			$I_{\rm F} = 3.0 \text{ mA}, I_{\rm C} = 1.6 \text{ mA}$	L	0.17	0.40		
			$I_{\rm F} = 1.0 \text{ mA}, I_{\rm C} = 0.45 \text{ mA}$			0.40		
		F0D8802D	$I_F = 1.6 \text{ mA}, I_C = 0.60 \text{ mA}$			0.40	-	
		1 000020	$I_F = 3.0 \text{ mA}, I_C = 1.00 \text{ mA}$			0.40	-	

Table 5. SWITCHING CHARACTERISTICS

Apply over all recommended conditions ($T_A = -40^{\circ}C$ to $+125^{\circ}C$ unless otherwise specified). All typical values are measured at $T_A = 25^{\circ}C$.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
÷	Turn On Time	I_F = 1.6 mA, V_{CC} = 5 V, R_L = 0.75 $k\Omega$	1	6	20	μs
t _{ON}		I_{F} = 1.6 mA, V_{CC} = 5 V, R_{L} = 4.7 $k\Omega$		6		μs
÷	Turn Off Time	I_F = 1.6 mA, V_{CC} = 5 V, R_L = 0.75 $k\Omega$	1	6	20	μs
tOFF		I_F = 1.6 mA, V_{CC} = 5 V, R_L = 4.7 k Ω		40		μs
t _R	Output Rise Time (10% –90%)	I_F = 1.6 mA, V_{CC} = 5 V, R_L = 0.75 $k\Omega$		6		μs
t _F	Output Fall Time (90% -10%)	I_F = 1.6 mA, V_{CC} = 5 V, R_L = 0.75 $k\Omega$		7		μs
CM _H	Common Mode Rejection Voltage (Transient Immunity Output High)	$I_F = 0$ mA, $V_{CC} = 5$ V, $R_L = 4.7$ kΩ VCM = 500 V (Note 3)		10		kV/μs
CML	Common Mode Rejection Voltage (Transient Immunity Output Low)	$I_{F} = 1.6 \text{ mA}, \text{ V}_{CC} = 5 \text{ V}, \text{ R}_{L} = 4.7 \text{ k}\Omega$ VCM = 500 V (Note 3)		10		kV/μs

3. Common mode transient immunity at output high is the maximum tolerable positive dVcm/dt on the leading edge of the common mode impulse signal, Vcm, to assure that the output will remain high.

Table 6. ISOLATION CHARACTERISTICS

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{ISO}	Input-Output Isolation Voltage	Freq = 60 Hz, t = 1.0 min, $I_{I-O} \leq$ 10 μA (Notes 4, 5)	2,500			VAC _{RMS}
R _{ISO}	Isolation Resistance	V _{I-O} = 500 V (Note 4)	10 ¹¹			Ω
C _{ISO}	Isolation Capacitance	Frequency = 1 MHz		0.6		pF

Device is considered a two terminal device: Pins 1 and 2 are shorted together and Pins 3 and 4 are shorted together.
2,500 VAC_{RMS} for 1 minute duration is equivalent to 3,000 VAC_{RMS} for 1 second duration.

TEST CIRCUIT



Figure 1. Switching Test Circuit and Waveform



Figure 2. Test Circuit for Instantaneous Common-Mode Rejection Voltage

TYPICAL PERFORMANCE CHARACTERISTICS



Figure 3. Forward Current vs. Forward Voltage



Figure 4. Collector Current vs. Forward Current



Figure 5. Current Transfer Ratio vs. Forward Current



Figure 7. Normalized CTR vs. Ambient Temperature



Figure 6. Normalized CTR vs. Forward Current



Temperature

TYPICAL PERFORMANCE CHARACTERISTICS (continued)







Figure 11. Collector Dark Current vs. Ambient Temperature



Gure 13. Collector Current vs Collector-Emitter Voltage



Figure 10. Current Transfer Ratio vs. Ambient Temperature



Figure 12. Collector–Emitter Saturation Voltage vs. Ambient Temperature



Figure 14. Switching Time vs. Load Resistance

REFLOW PROFILE



Figure 15. Reflow Profile

Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60–120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

ORDERING INFORMATION (Note 6)

Part Number	Package	Packing Method
FOD8802A	Small Outline 8-Pin	Tube (100 units per tube)
FOD8802AR2	Small Outline 8-Pin	Tape and Reel (2,500 units per reel)
FOD8802AV	Small Outline 8-Pin DIN EN/IEC60747-5-5 Option (pending approval)	Tube (100 units per tube)
FOD8802AR2V	Small Outline 8-Pin DIN EN/ IEC60747-5-5 Option (pending approval)	Tape and Reel (2,500 units per reel)

6. The product orderable part number system listed in this table also applies to the FOD8802A, FOD8802B, FOD8802C and FOD8802D products.

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